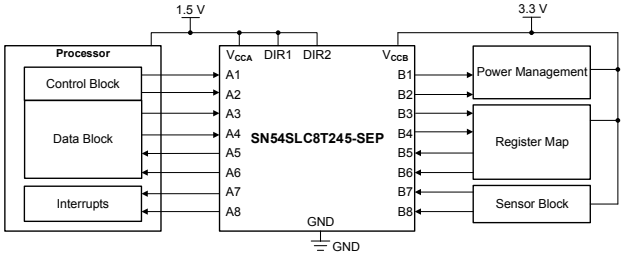
SN54SLC8T245-SEP 8 ビット、デュアル電源バス・トランシーバ、構成可能な電圧変換およびトライステート出力搭載

1 特長

- VID V62/22604
- 耐放射線特性:
  - 125℃において 43MeV-cm^2/mg のシングル・イベント・ラッチアップ (SEL) 耐性
  - すべてのウェハー・ロットについて、20krad(Si) までの吸収線量 (TID) RLAT (Radiation Lot Acceptance Test)
- 認定済みの完全に構成可能なデュアル・レール設計により、各ポートは 0.65V～3.6V の範囲の電源電圧で動作可能
- 動作温度範囲:–55℃～+125℃
- 複数の方向制御ピンにより、昇圧と降圧の変換を同時に実行
- 1.8V から 3.3V への変換時に最高 380Mbps をサポート
- 電源オフ時に 2 つのバスを実質的に絶縁する V_{CC} 絶縁機能
- 部分的パワーダウン・モードにより、電源オフ時に電流の逆流を制限
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
  - 人体モデルで 8000V
  - デバイス帯電モデルで 1000V

2 アプリケーション

- 低軌道 (LEO) 衛星用途のサポート
- 宇宙用レーダーおよび通信
- 人工衛星のペイロード



代表的なアプリケーション回路図

3 概要

SN54SLC8T245-SEP デバイスは、8 ビットの非反転バス・トランシーバで、最新の電圧ノード (0.7V、0.8V、0.9V) で動作しているデバイスと、業界標準の電圧ノード (1.8V、2.5V、3.3V) で動作しているデバイスとの間で、電圧レベル不一致の問題を双方向に解決できます。

このデバイスは、2 つの独立した電源レール (V_{CCA} および V_{CCB}) を使用し、最低 0.65V で動作します。データ・ピン A1 から A8 までは V_{CCA} に追従するように設計されており、0.65V～3.6V の任意の電源電圧を受け付けます。データ・ピン B1 から B8 までは V_{CCB} に追従するように設計されており、0.65V～3.6V の任意の電源電圧を受け付けます。

SN54SLC8T245-SEP は、データ・バス間の非同期通信用に設計されています。このデバイスは、方向制御入力 (DIR1 および DIR2) のロジック・レベルに応じて、A バスから B バスへ、または B バスから A バスへデータを転送します。出力イネーブル ($\overline{OE}$) 入力を使用すると、出力をディスエーブルにして、バスを実質的に絶縁できます。

SN54SLC8T245-SEP デバイスは、制御ピン (DIR および $\overline{OE}$) が V_{CCA} を基準とするよう設計されています。

このデバイスは、I_{off} を使用する部分的パワーダウン・アプリケーション用の動作が完全に規定されています。I_{off} 回路は、デバイスの電源がオフになったとき、出力をディセーブルにします。これによってデバイスへの電流の逆流を阻止し、デバイスを損傷から保護します。

V_{CC} 絶縁機能により、いずれかの V_{CC} 入力電圧が 100mV 未満になると、すべてのレベル シフタ出力がディセーブルされ、高インピーダンス状態になるように設計されています。

電源投入または電源オフの間にレベル シフタ I/O を高インピーダンス状態にするには、$\overline{OE}$ をプルアップ抵抗を介して V_{CC} に接続します。この抵抗の最小値は、ドライバの電流シンク能力によって決まります。

パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ (2)
SN54SLC8T245-SEP	PW (TSSOP、24)	7.8mm × 6.4mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。

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4 Pin Configuration and Functions

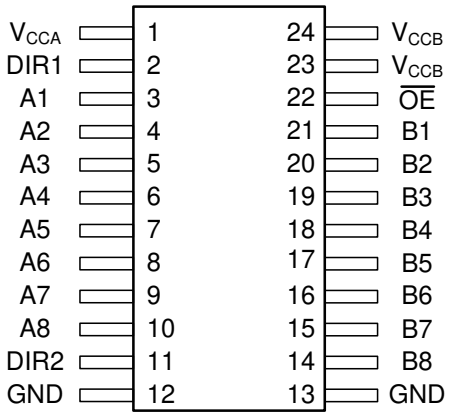


図 4-1. PW Package, 24-Pin TSSOP (Top View)

表 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
A1	3	I/O	Input/output A1. Referenced to V_{CCA}.
A2	4	I/O	Input/output A2. Referenced to V_{CCA}.
A3	5	I/O	Input/output A3. Referenced to V_{CCA}.
A4	6	I/O	Input/output A4. Referenced to V_{CCA}.
A5	7	I/O	Input/output A5. Referenced to V_{CCA}.
A6	8	I/O	Input/output A6. Referenced to V_{CCA}.
A7	9	I/O	Input/output A7. Referenced to V_{CCA}.
A8	10	I/O	Input/output A8. Referenced to V_{CCA}.
B1	21	I/O	Input/output B1. Referenced to V_{CCB}.
B2	20	I/O	Input/output B2. Referenced to V_{CCB}.
B3	19	I/O	Input/output B3. Referenced to V_{CCB}.
B4	18	I/O	Input/output B4. Referenced to V_{CCB}.
B5	17	I/O	Input/output B5. Referenced to V_{CCB}.
B6	16	I/O	Input/output B6. Referenced to V_{CCB}.
B7	15	I/O	Input/output B7. Referenced to V_{CCB}.
B8	14	I/O	Input/output B8. Referenced to V_{CCB}.
DIR1	2	I	Direction-control signal 1. Referenced to V_{CCA}.
DIR2	11	I	Direction-control signal 2. Referenced to V_{CCA}. Tie to GND to maintain backward compatibility with SN74AVC8T245 device.
GND	12	—	Ground
	13	—	Ground
$\overline{OE}$	22	I	Output Enable. Pull to GND to enable all outputs. Pull to V_{CCA} to place all outputs in high-impedance mode. Referenced to V_{CCA}.
V_{CCA}	1	—	A-port supply voltage. 0.65 V ≤ V_{CCA} ≤ 3.6 V
V_{CCB}	23	—	B-port supply voltage. 0.65 V ≤ V_{CCB} ≤ 3.6 V
	24	—	B-port supply voltage. 0.65 V ≤ V_{CCB} ≤ 3.6 V

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V_{CCA}		–0.5	4.2	V
Supply voltage, V_{CCB}		–0.5	4.2	V
Input voltage, V_I (2)	I/O ports (A port)	–0.5	4.2	V
	I/O ports (B port)	–0.5	4.2	
	Control inputs	–0.5	4.2	
Voltage applied to any output in the high-impedance or power-off state, V_O (2)	A port	–0.5	4.2	V
	B port	–0.5	4.2	
Voltage applied to any output in the high or low state, V_O (2) (3)	A port	–0.5	V_{CCA} + 0.2	V
	B port	–0.5	V_{CCB} + 0.2	
Input clamp current, I_{IK}	V_I < 0	–50		mA
Output clamp current, I_{OK}	V_O < 0	–50		mA
Continuous output current, I_O		–50	50	mA
Continuous current through V_{CCA}, V_{CCB}, or GND		–100	100	mA
Junction Temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The output positive-voltage rating may be exceeded up to 4.2 V maximum if the output current rating is observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±8000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

				MIN	MAX	UNIT
V_{CCA}	Supply voltage			0.65	3.6	V
V_{CCB}	Supply voltage			0.65	3.6	V
V_{IH}	High-level input voltage	Data inputs	V_{CCI} = 0.65 V – 0.75 V	V_{CCI} × 0.70		V
			V_{CCI} = 0.76 V – 1 V	V_{CCI} × 0.70		
			V_{CCI} = 1.1 V – 1.95 V	V_{CCI} × 0.65		
			V_{CCI} = 2.3 V – 2.7 V	1.6		
			V_{CCI} = 3 V – 3.6 V	2		
		Control inputs (DIR, $\overline{OE}$) Referenced to V_{CCA}	V_{CCA} = 0.65 V – 0.75 V	V_{CCA} × 0.70		
			V_{CCA} = 0.76 V – 1 V	V_{CCA} × 0.70		
			V_{CCA} = 1.1 V – 1.95 V	V_{CCA} × 0.65		
			V_{CCA} = 2.3 V – 2.7 V	1.6		
			V_{CCA} = 3 V – 3.6 V	2		
V_{IL}	Low-level input voltage	Data inputs	V_{CCI} = 0.65 V – 0.75 V		V_{CCI} × 0.30	V
			V_{CCI} = 0.76 V – 1 V		V_{CCI} × 0.30	
			V_{CCI} = 1.1 V – 1.95 V		V_{CCI} × 0.35	
			V_{CCI} = 2.3 V – 2.7 V		0.7	
			V_{CCI} = 3 V – 3.6 V		0.8	
		Control inputs (DIR, $\overline{OE}$) Referenced to V_{CCA}	V_{CCA} = 0.65 V – 0.75 V		V_{CCA} × 0.30	
			V_{CCA} = 0.76 V – 1 V		V_{CCA} × 0.30	
			V_{CCA} = 1.1 V – 1.95 V		V_{CCA} × 0.35	
			V_{CCA} = 2.3 V – 2.7 V		0.7	
			V_{CCA} = 3 V – 3.6 V		0.8	
V_I	Input voltage(3)			0	3.6	V
V_O	Output voltage	Active state		0	V_{CCO} (2)	V
		Tri-state		0	3.6	
Δt/Δv	Input transition rise or fall rate				10	ns/V
T_A	Operating free-air temperature			–55	125	°C

(1) V_{CCI} is the V_{CC} associated with the input port.
(2) V_{CCO} is the V_{CC} associated with the output port.
(3) All unused data inputs of the device must be held at V_{CCI} or GND for proper device operation. See the *Implications of Slow or Floating CMOS Inputs* application report.

5.4 Thermal Information

THERMAL METRIC		SN54SLC8T245-SEP PW (TSSOP) 24 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	45.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	58.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	6.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	57.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

5.5 Electrical Characteristics

Over recommended operating free-air temperature range (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		V_{CCA}	V_{CCB}	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	$V_I = V_{IH}$	I_{OH} = –100 µA	0.7 V – 3.6 V	0.7 V – 3.6 V	V_{CCO} – 0.1			V
			I_{OH} = –50 µA	0.65 V	0.65 V	0.55			
			I_{OH} = –200 µA	0.76 V	0.76 V	0.58			
			I_{OH} = –500 µA	0.85 V	0.85 V	0.65			
			I_{OH} = -3 mA	1.1 V	1.1 V	0.85			
			I_{OH} = -6 mA	1.4 V	1.4 V	1.05			
			I_{OH} = -8 mA	1.65 V	1.65 V	1.2			
			I_{OH} = -9 mA	2.3 V	2.3 V	1.75			
			I_{OH} = -12 mA	3 V	3 V	2.3			
V_{OL}	Low-level output voltage	$V_I = V_{IL}$	I_{OL} = 100 µA	0.7 V – 3.6 V	0.7 V – 3.6 V			0.1	V
			I_{OL} = 50 µA	0.65 V	0.65 V			0.1	
			I_{OL} = 200 µA	0.76 V	0.76 V			0.18	
			I_{OL} = 500 µA	0.85 V	0.85 V			0.2	
			I_{OL} = 3 mA	1.1 V	1.1 V			0.25	
			I_{OL} = 6 mA	1.4 V	1.4 V			0.35	
			I_{OL} = 8 mA	1.65 V	1.65 V			0.45	
			I_{OL} = 9 mA	2.3 V	2.3 V			0.55	
			I_{OL} = 12 mA	3 V	3 V			0.7	
I_I	Input leakage current	Control Inputs (DIR, $\overline{OE}$): $V_I = V_{CCA}$ or GND		0.65 V – 3.6 V	0.65 V – 3.6 V	−1		1	µA
I_{off}	Partial power down current	A Port: V_I or V_O = 0 V – 3.6 V		0 V	0 V – 3.6 V	−35		55	µA
		B Port: V_I or V_O = 0 V – 3.6 V		0 V – 3.6 V	0 V	−35		55	
I_{OZ}	High-impedance state output current	A Port: $V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND, $\overline{OE} = V_{IH}$		3.6 V	3.6 V	−8		8	µA
		B Port: $V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND, $\overline{OE} = V_{IH}$		3.6 V	3.6 V	−8		8	
I_{CCA}	V_{CCA} supply current	$V_I = V_{CCI}$ or GND, I_O = 0 mA		0.65 V – 3.6 V	0.65 V – 3.6 V			40	µA
				0 V	3.6 V	−12			
				3.6 V	0 V			35	
I_{CCB}	V_{CCB} supply current	$V_I = V_{CCI}$ or GND, I_O = 0 mA		0.65 V – 3.6 V	0.65 V – 3.6 V			38	µA
				0 V	3.6 V			35	
				3.6 V	0 V	−12			
I_{CCA} + I_{CCB}	Combined supply current	$V_I = V_{CCI}$ or GND, I_O = 0 mA		0.65 V – 3.6 V	0.65 V – 3.6 V			70	µA
C_i	Input capacitance	Control Inputs (DIR, $\overline{OE}$): V_I = 3.3 V or GND		3.3 V	3.3 V		4.5		pF
C_{io}	Data I/O capacitance	Ports A and B: $\overline{OE} = V_{CCA}$, V_O = 1.65 V DC + 1 MHz -16 dBm sine wave		3.3 V	3.3 V		5.7		pF

(1) V_{CCO} is the V_{CC} associated with the output port.
(2) All typical values are for T_A = 25°C

5.6 Switching Characteristics, V_{CCA} = 0.7 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	68	47	34	23	21	21	23	27	ns
		From input B to output A	67	55	46	32	28	26	25	25	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	100	100	100	100	100	100	100	100	ns
		From input $\overline{OE}$ to output B	111	86	73	38	34	34	33	36	
t_{en}	Enable time	From input $\overline{OE}$ to output A	105	105	105	105	105	105	105	105	ns
		From input $\overline{OE}$ to output B	127	78	56	39	36	36	39	47	

5.7 Switching Characteristics, V_{CCA} = 0.8 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	55	38	26	16	14	13	13	14	ns
		From input B to output A	47	38	32	21	17	15	14	14	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	71	71	71	71	71	71	71	71	ns
		From input $\overline{OE}$ to output B	105	79	66	32	28	27	25	26	
t_{en}	Enable time	From input $\overline{OE}$ to output A	64	64	64	64	64	64	64	64	ns
		From input $\overline{OE}$ to output B	118	69	47	30	27	26	26	28	

5.8 Switching Characteristics, V_{CCA} = 0.9 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	45	31	21	13	10	9	9	9	ns
		From input B to output A	35	27	23	15	11	10	9	8	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	55	55	55	55	55	55	55	55	ns
		From input $\overline{OE}$ to output B	99	74	61	26	23	22	20	20	
t_{en}	Enable time	From input $\overline{OE}$ to output A	41	41	41	41	41	41	41	41	ns
		From input $\overline{OE}$ to output B	108	63	41	24	20	19	18	19	

5.9 Switching Characteristics, V_{CCA} = 1.2 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	33	21	14	8	6	5	5	5	ns
		From input B to output A	24	16	13	8	6	5	4	4	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	19	19	19	19	19	19	19	19	ns
		From input $\overline{OE}$ to output B	92	66	53	20	17	16	14	14	
t_{en}	Enable time	From input $\overline{OE}$ to output A	19	19	19	19	19	19	19	19	ns
		From input $\overline{OE}$ to output B	96	53	33	17	12	11	10	10	

5.10 Switching Characteristics, V_{CCA} = 1.5 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	29	17	11	6	5	4	4	3	ns
		From input B to output A	23	14	10	6	5	4	3	3	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	15	15	15	15	15	15	15	15	ns
		From input $\overline{OE}$ to output B	89	64	50	18	15	15	12	13	
t_{en}	Enable time	From input $\overline{OE}$ to output A	12	12	12	12	12	12	12	12	ns
		From input $\overline{OE}$ to output B	92	49	29	14	10	8	7	7	

5.11 Switching Characteristics, V_{CCA} = 1.8 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	28	15	9	5	4	4	3	3	ns
		From input B to output A	23	13	9	5	4	4	3	2	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	14	14	14	14	14	14	14	14	ns
		From input $\overline{OE}$ to output B	89	63	49	17	15	14	12	12	
t_{en}	Enable time	From input $\overline{OE}$ to output A	9	9	9	9	9	9	9	9	ns
		From input $\overline{OE}$ to output B	91	47	28	13	9	7	6	6	

5.12 Switching Characteristics, V_{CCA} = 2.5 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	27	14	8	4	3	3	2	2	ns
		From input B to output A	26	13	8	5	4	3	2	2	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	11	11	11	11	11	11	11	11	ns
		From input $\overline{OE}$ to output B	88	62	48	16	13	13	11	11	
t_{en}	Enable time	From input $\overline{OE}$ to output A	6	6	6	6	6	6	6	6	ns
		From input $\overline{OE}$ to output B	89	46	26	12	8	7	5	5	

5.13 Switching Characteristics, V_{CCA} = 3.3 V

See 図 6-1 and 図 6-2 for test circuit and loading conditions. See 図 6-3 and 図 6-4 for measurement waveforms.

PARAMETER		TEST CONDITIONS	B-PORT SUPPLY VOLTAGE (V_{CCB})								UNIT
			0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
t_{pd}	Propagation delay	From input A to output B	27	13	8	4	3	2	2	2	ns
		From input B to output A	31	14	9	5	3	3	2	2	
t_{dis}	Disable time	From input $\overline{OE}$ to output A	11	11	11	11	11	11	11	11	ns
		From input $\overline{OE}$ to output B	87	61	48	16	13	12	11	11	
t_{en}	Enable time	From input $\overline{OE}$ to output A	5	5	5	5	5	5	5	5	ns
		From input $\overline{OE}$ to output B	89	45	26	11	8	6	5	4	

5.14 Operating Characteristics

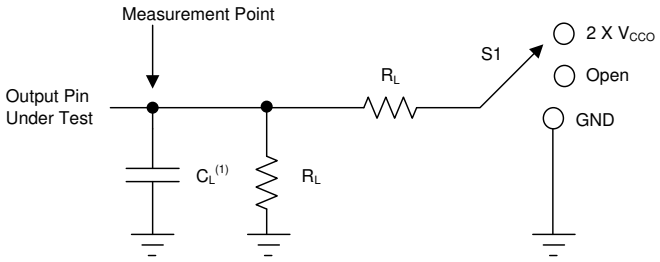
T_A = 25°C, C_L = 0, R_L = Open, f = 1 MHz, t_r = t_f = 1 ns

PARAMETER		TEST CONDITIONS	SUPPLY VOLTAGE (V_{CCA} = V_{CCB})								UNIT
			0.7 V	0.8 V	0.9 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
C_{pdA}	V_{CCA} Power dissipation capacitance per transceiver	A to B: Outputs Enabled	1.2	1.8	1.8	1.7	1.7	1.7	2	2.5	pF
		A to B: Outputs Disabled	1.1	1.8	1.8	1.7	1.7	1.7	2	2.1	pF
		B to A: Outputs Enabled	9.3	11.8	11.8	12	12.2	13	16.4	18.1	pF
		B to A: Outputs Disabled	2.6	1.2	1.1	1.2	1.2	1.3	1.6	3.9	pF
C_{pdB}	V_{CCB} Power dissipation capacitance per transceiver	A to B: Outputs Enabled	9.3	11.7	11.8	11.9	12.2	12.9	16.3	18	pF
		A to B: Outputs Disabled	2.6	11.7	11.8	11.9	12.2	12.9	16.3	3.9	pF
		B to A: Outputs Enabled	1.2	1.8	1.8	1.7	1.7	1.7	2	2.5	pF
		B to A: Outputs Disabled	1.1	1.8	1.8	1.7	1.7	1.7	2	2.1	pF

6 Parameter Measurement Information

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f =1 MHz
- Z_0 = 50 Ω
- dv / dt ≤ 1 ns/V



A. C_L includes probe and jig capacitance.

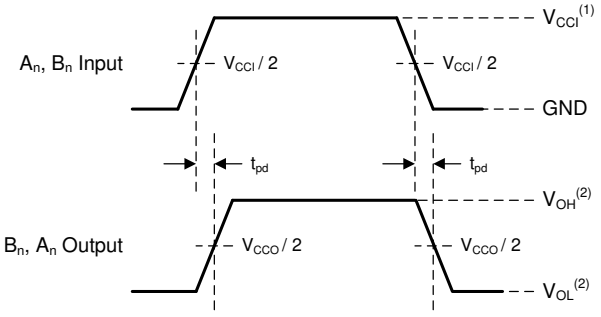
図 6-1. Load Circuit

Parameter	V_{CCO}	R_L	C_L	S1	V_{TP}
t_{pd}	1.1 V - 3.6 V	2 kΩ	15 pF	Open	N/A
	0.65 V - 0.95 V	20 kΩ	15 pF	Open	N/A
t_{en}(1), t_{dis}(1)	3 V - 3.6 V	2 kΩ	15 pF	2 X V_{CCO}	0.3 V
	1.65 V - 2.7 V	2 kΩ	15 pF	2 X V_{CCO}	0.15 V
	1.1 V - 1.6 V	2 kΩ	15 pF	2 X V_{CCO}	0.1 V
	0.65 V - 0.95 V	20 kΩ	15 pF	2 X V_{CCO}	0.1 V
t_{en}(2), t_{dis}(2)	3 V - 3.6 V	2 kΩ	15 pF	GND	0.3 V
	1.65V - 2.7 V	2 kΩ	15 pF	GND	0.15 V
	1.1 V - 1.6 V	2 kΩ	15 pF	GND	0.1 V
	0.65 V - 0.95 V	20 kΩ	15 pF	GND	0.1 V

A. Output waveform on the conditions that input is driven to a valid Logic Low.

B. Output waveform on the condition that input is driven to a valid Logic High.

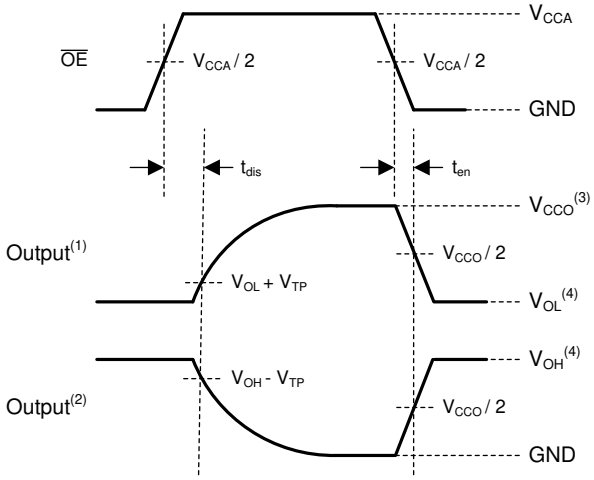
図 6-2. Load Circuit Conditions



A. V_{CCI} is the supply pin associated with the input port.

B. V_{OH} and V_{OL} are typical output voltage levels with specified R_L, C_L, and S_1.

図 6-3. Propagation Delay



A. Output waveform on the condition that input is driven to a valid Logic Low.

B. Output waveform on the condition that input is driven to a valid Logic High.

C. V_{CCO} is the supply pin associated with the output port.

D. V_{OH} and V_{OL} are typical output voltage levels with specified R_L, C_L, and S_1.

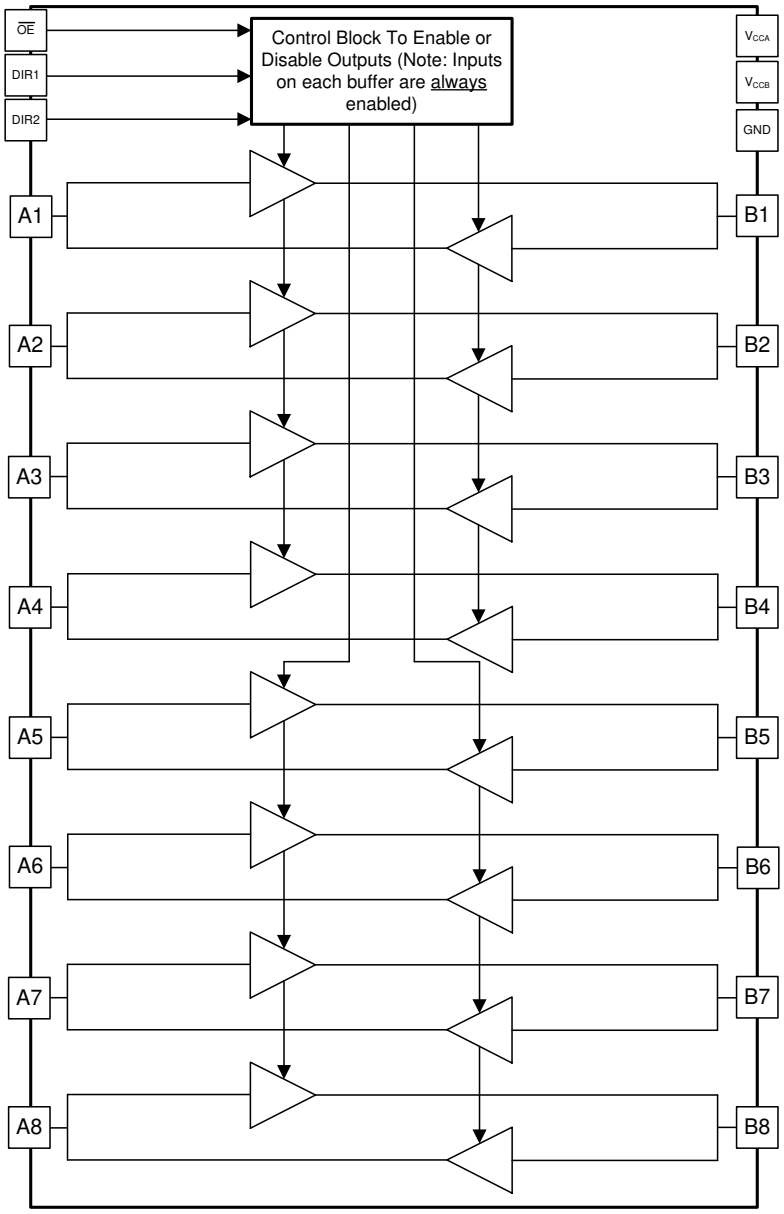
図 6-4. Enable Time And Disable Time

7 Detailed Description

7.1 Overview

The SN54SLC8T245-SEP device is an 8-bit, dual-supply non-inverting transceiver with bidirectional voltage level translation. The I/O pins labeled with A and the control pins (DIR1, DIR2, and $\overline{OE}$) are supported by V_{CCA}, and the I/O pins labeled with B are supported by V_{CCB}. The A port and the B port are able to accept I/O voltages ranging from 0.65 V to 3.6 V.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Up-Translation and Down-Translation From 0.65 V to 3.6 V

Both supply pins are configured from 0.65 V to 3.6 V, which makes the device suitable for translating between any of the low voltage nodes (0.7 V, 0.8 V, 0.9 V, 1.2 V, 1.8 V, 2.5 V, and 3.3 V).

7.3.2 Multiple Direction Control Pins

Two control pins are used to configure the 8 data I/Os. I/O channels 1 through 4 are grouped together and I/O channels 5 through 8 are banked together. The benefit of this is to permit simultaneous up-translation and down-translation within one device. This eliminates the need for multiple devices, where each device can only provide up-translation or down-translation sequentially. Simultaneous up and down translation is supported when both V_{CCA} and V_{CCB} are at least 1.40 V.

7.3.3 I_{off} Supports Partial-Power-Down Mode Operation

This feature is to limit the leakage current of an I/O pin being driven to a voltage as large as 3.6 V while having its corresponding power supply rail powered down. This is represented by the I_{off} parameter in the *Electrical Characteristics* table.

7.4 Device Functional Modes

All control inputs are referenced to V_{CCA} and must be driven to a valid Logic High or Logic Low (that is, not floating) for proper device operation and to prevent excessive power consumption. 表 7-1 summarizes the possible modes of device operation based on the configuration of the control inputs.

表 7-1. Function Table

CONTROL INPUTS(1)			SIGNAL DIRECTION	
$\overline{OE}$	DIR1	DIR2	Bits 1:4	Bits 5:8
H	X	X	Disabled (Hi-Z)	
L	L	L	B to A	
L	L	H	B to A	A to B
L	H	L	A to B	
L	H	H	A to B	B to A

(1) Input circuits of the data I/Os are always active and must be driven to a valid logic level.

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN54SLC8T245-SEP device can be used in level-translation applications for interfacing devices or systems operating at different voltage nodes. 図 8-1 depicts an application in which the SN54SLC8T245-SEP device is up-translating a 0.7 V input to a 3.3 V output to interface between a system controller and a peripheral device.

8.2 Typical Application

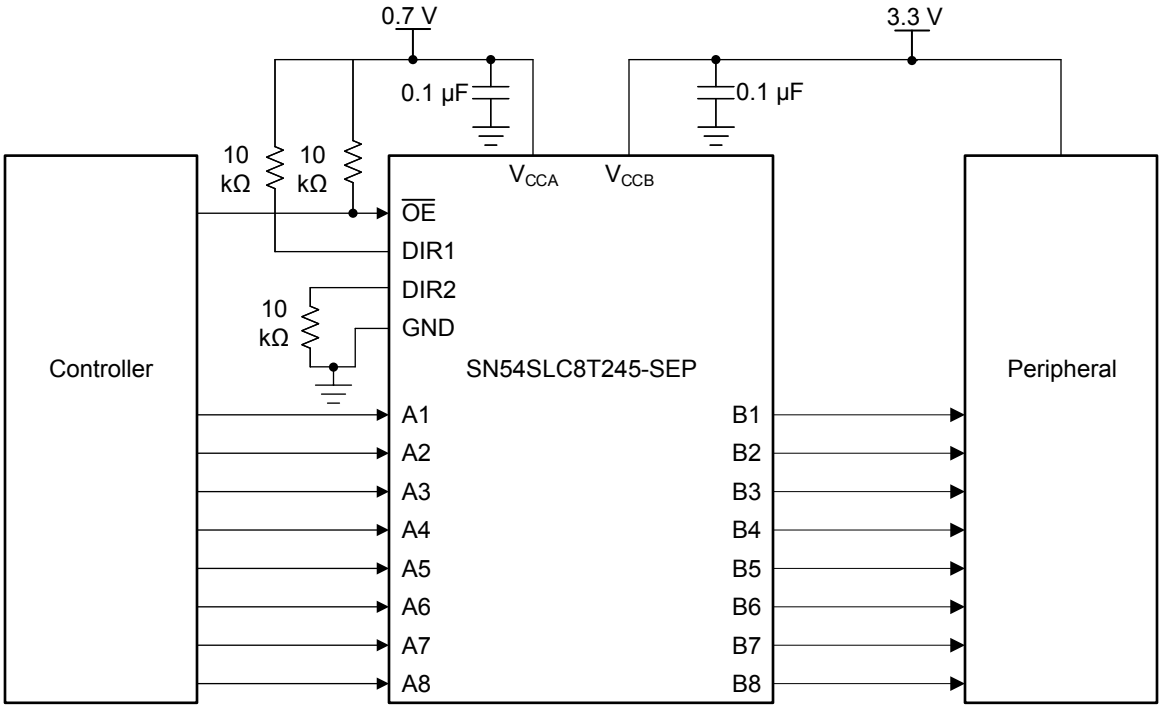


図 8-1. Typical Application Schematic

8.2.1 Design Requirements

For this design example, use the parameters listed in 表 8-1.

表 8-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUE
Input voltage range	0.65 V to 3.6 V
Output voltage range	0.65 V to 3.6 V

8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN54SLC8T245-SEP device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN54SLC8T245-SEP device is driving to determine the output voltage range.

8.2.3 Application Curve

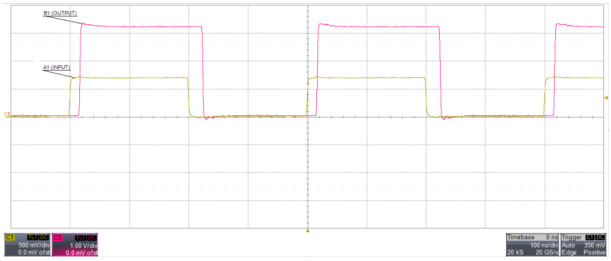


図 8-2. Translation Up (0.7 V to 3.3 V) at 2.5 MHz

8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. There are no additional requirements for power supply sequencing.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices. For more information regarding the power up glitch performance of level translators, see the *Power Sequencing for AXC Family of Devices* application report.

8.4 Layout

8.4.1 Layout Guidelines

To device reliability, follow common printed-circuit board layout guidelines:

- Use bypass capacitors on power supplies.
- Use short trace lengths to avoid excessive loading.
- Place pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.

8.4.2 Layout Example

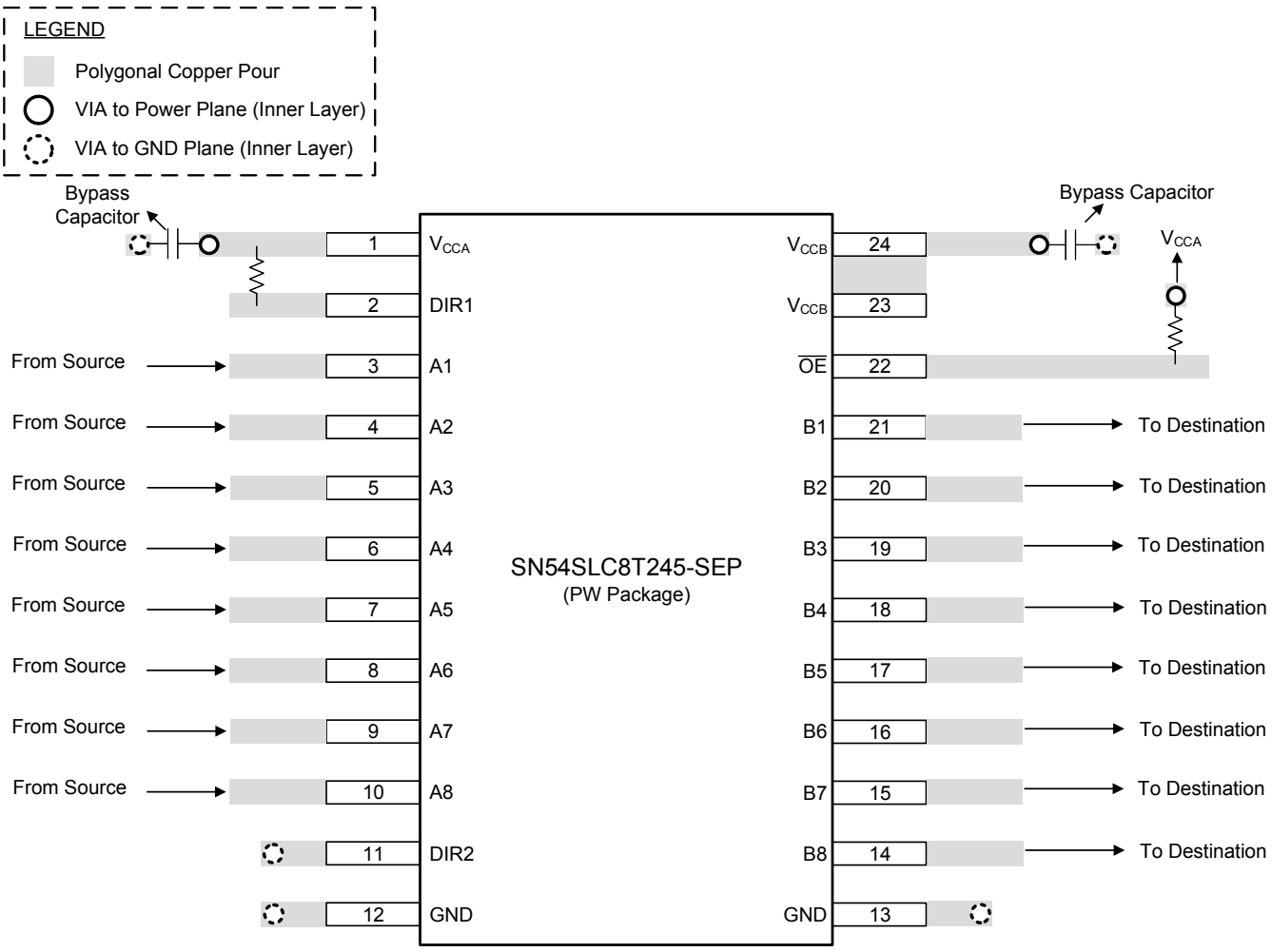


図 8-3. SN54SLC8T245-SEP Device Layout Example

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application report

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (September 2022) to Revision B (December 2023)	Page
• パッケージ・リード・サイズを含めるよう「パッケージ情報」表を更新	1
• Updated the *Translation Up (0.7 V to 3.3 V) at 2.5 MHz* figure	14

Changes from Revision * (February 2022) to Revision A (September 2022)	Page
• データシートのステータスを以下のように変更：「事前情報」から「*量産データ*」	1

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN54SLC8T245PWTSEP	Active	Production	TSSOP (PW) | 24	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	SLC8T245E
V62/22604-01XE	Active	Production	TSSOP (PW) | 24	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	See SN54SLC8T245PWTSEP	SLC8T245E

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

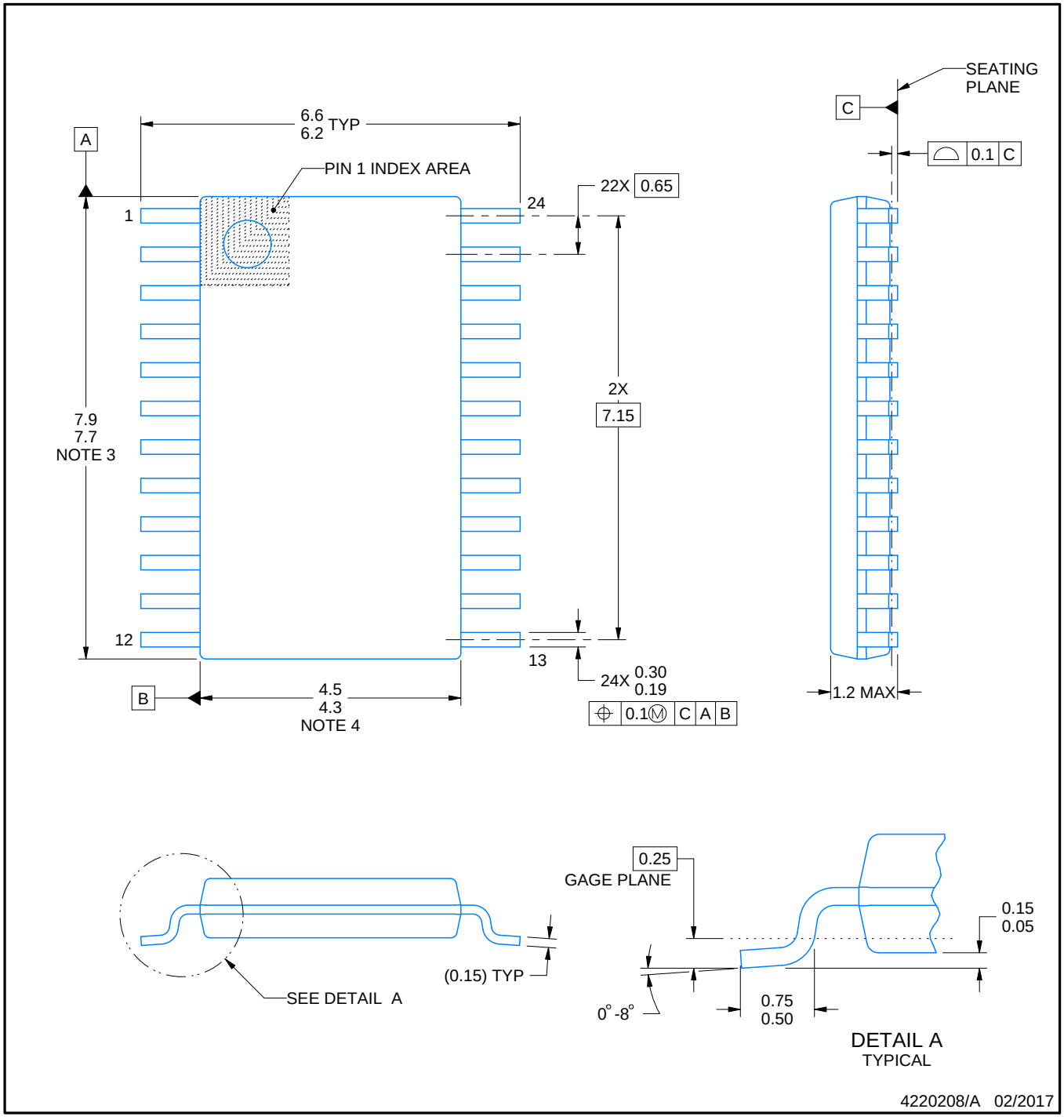
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

PACKAGE OUTLINE

PW0024A

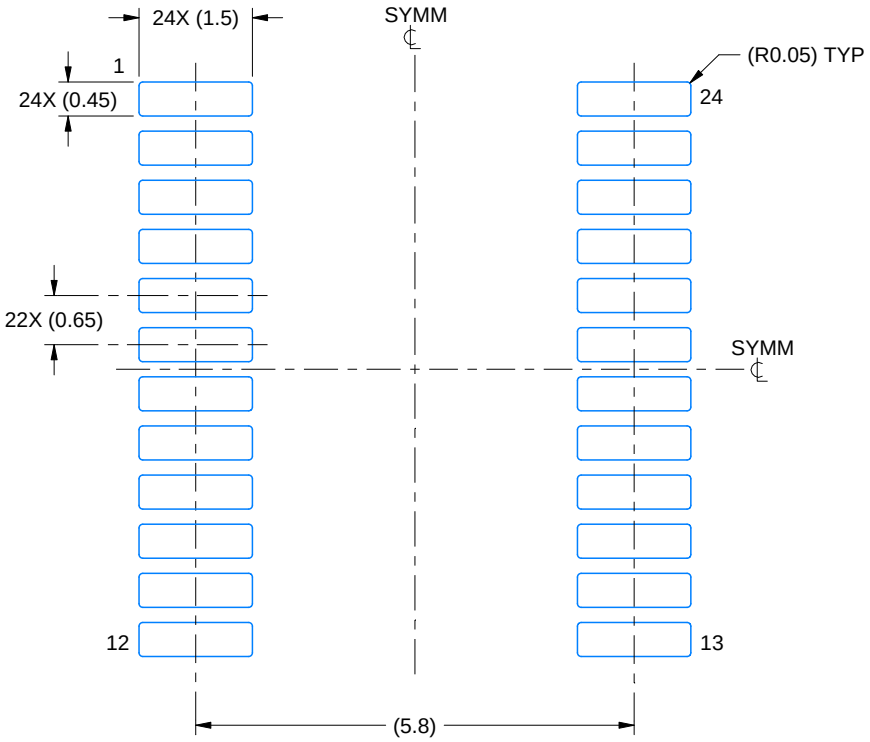
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

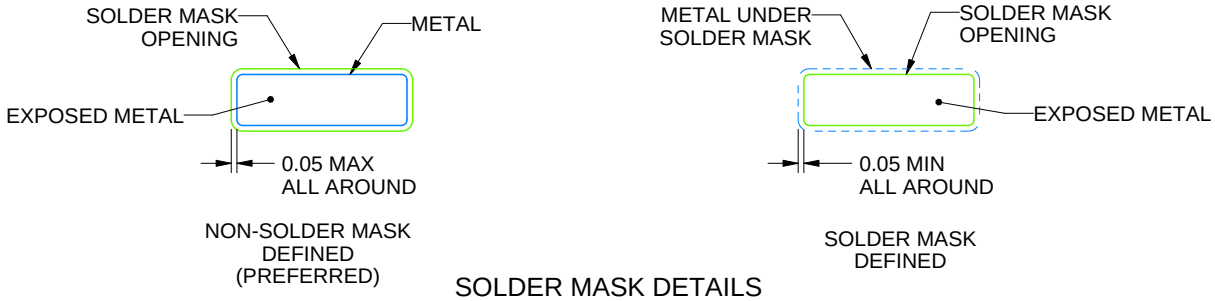


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

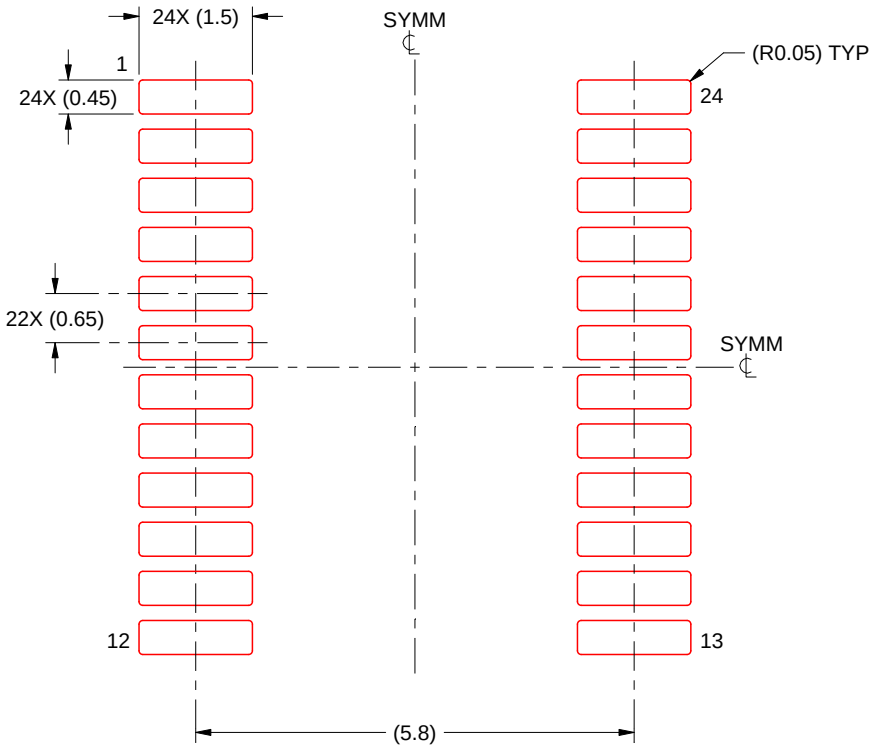


SOLDER MASK DETAILS

4220208/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220208/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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